

# SKM200GB12V



**SEMITRANS® 3**

## SKM200GB12V

### Features

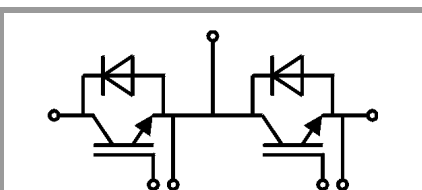
- V-IGBT = 6. Generation Trench V-IGBT (Fuji)
- CAL4 = Soft switching 4. Generation CAL-diode
- Isolated copper baseplate using DBC technology (Direct Copper Bonding)
- UL recognized, file no. E63532
- Increased power cycling capability
- With integrated gate resistor
- Low switching losses at high di/dt

### Typical Applications\*

- AC inverter drives
- UPS
- Electronic welders

### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max, recomm.  $T_{op} = -40 \dots +150^\circ\text{C}$ , product rel. results valid for  $T_j = 150^\circ$



**GB**

Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	311	A
		$T_c = 80^\circ\text{C}$	237	A
$I_{Cnom}$		200	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	600	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 720\text{ V}$	$T_j = 125^\circ\text{C}$	10	$\mu\text{s}$
	$V_{GE} \leq 20\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
$T_j$		-40 ... 175		$^\circ\text{C}$
<b>Inverse diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	229	A
		$T_c = 80^\circ\text{C}$	172	A
$I_{Fnom}$		200	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	600	A	
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	990	A	
$T_j$		-40 ... 175		$^\circ\text{C}$
<b>Module</b>				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	500	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50Hz, $t = 1\text{ min}$	4000	V	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 200\text{ A}$ $V_{GE} = 15\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	1.75	2.20	V
		$T_j = 150^\circ\text{C}$	2.20	2.50	V
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0.94	1.04	V
		$T_j = 150^\circ\text{C}$	0.88	0.98	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	4.05	5.8	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	6.60	7.60	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 8\text{ mA}$	5.5	6	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	$\text{mA}$
		$T_j = 150^\circ\text{C}$			$\text{mA}$
$C_{ies}$	$V_{CE} = 25\text{ V}$		12.02		nF
$C_{oes}$	$V_{GE} = 0\text{ V}$		1.18		nF
$C_{res}$			1.178		nF
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		2210		nC
$R_{Gint}$			3.8		$\Omega$
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 200\text{ A}$	$T_j = 150^\circ\text{C}$	320		ns
$t_r$	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	45		ns
$E_{on}$	$R_{Gon} = 3\ \Omega$	$T_j = 150^\circ\text{C}$	14		mJ
$t_{d(off)}$	$R_{Goff} = 3\ \Omega$	$T_j = 150^\circ\text{C}$	550		ns
$t_f$	$di/dt_{on} = 7000\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	72		ns
$E_{off}$	$di/dt_{off} = 2300\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	22		mJ
	$du/dt_{off} = 6900\text{ V}/\mu\text{s}$				
$R_{th(j-c)}$	per IGBT			0.14	K/W

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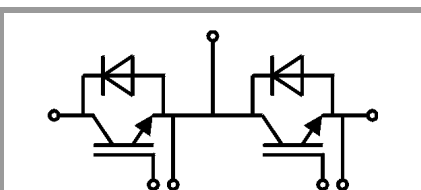
### Typical Applications\*

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- UPS
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### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max, recomm.  
 $T_{op} = -40 \dots +150^\circ\text{C}$ , product rel. results valid for  $T_j = 150^\circ$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse diode</b>						
$V_F = V_{EC}$	$I_F = 200\text{ A}$ $V_{GE} = 0\text{ V}$ chip	$T_j = 25^\circ\text{C}$		2.20	2.52	V
		$T_j = 150^\circ\text{C}$		2.15	2.47	V
$V_{F0}$		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$		4.5	5.1	m $\Omega$
		$T_j = 150^\circ\text{C}$		6.3	6.8	m $\Omega$
$I_{RRM}$	$I_F = 200\text{ A}$	$T_j = 150^\circ\text{C}$		230		A
$Q_{rr}$	$di/dt_{off} = 5300\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		30		$\mu\text{C}$
$E_{rr}$	$V_{GE} = \pm 15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		13		mJ
$R_{th(j-c)}$	per diode				0.26	K/W
<b>Module</b>						
$L_{CE}$				15	20	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.25		m $\Omega$
		$T_c = 125^\circ\text{C}$		0.5		m $\Omega$
$R_{th(c-s)}$	per module			0.02	0.038	K/W
$M_s$	to heat sink M6			3	5	Nm
$M_t$		to terminals M6		2.5	5	Nm
						Nm
$w$					325	g



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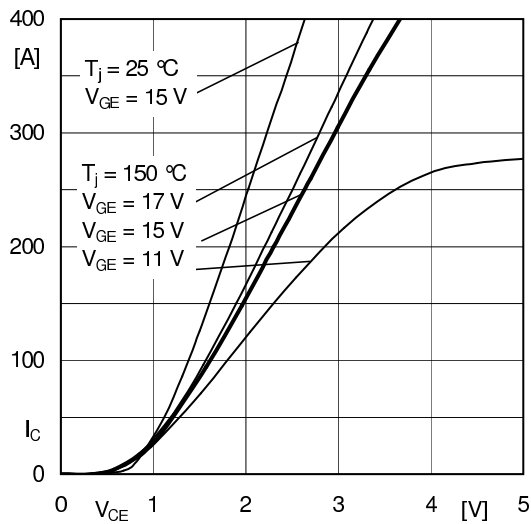


Fig. 1: Typ. output characteristic, inclusive  $R_{CC+EE}$

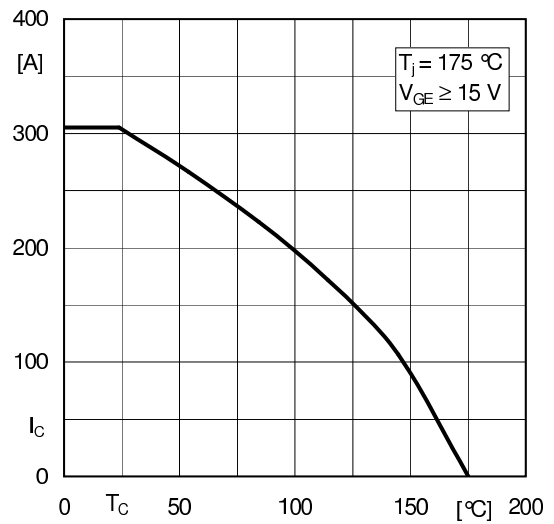


Fig. 2: Rated current vs. temperature  $I_C = f(T_C)$

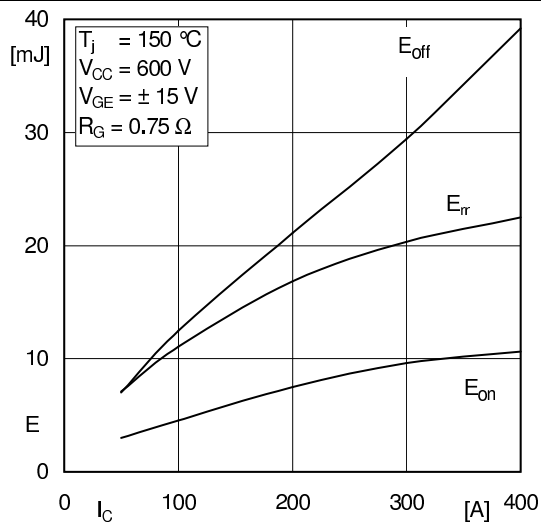


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

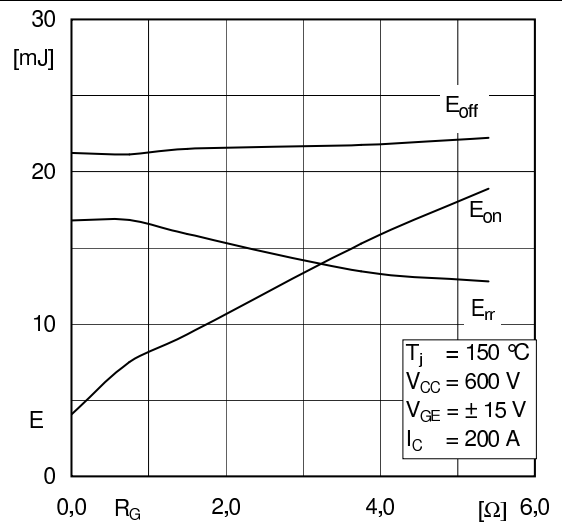


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

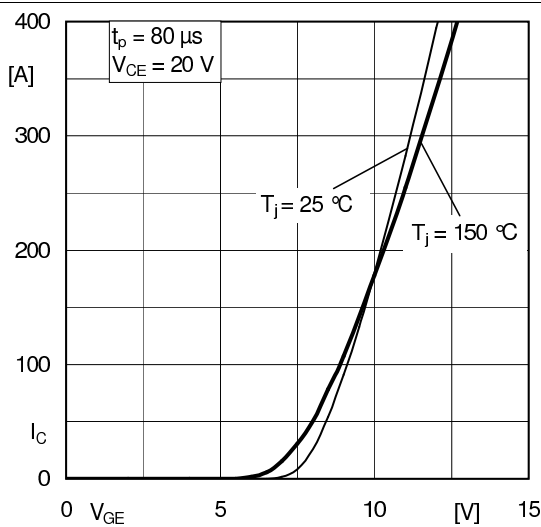


Fig. 5: Typ. transfer characteristic

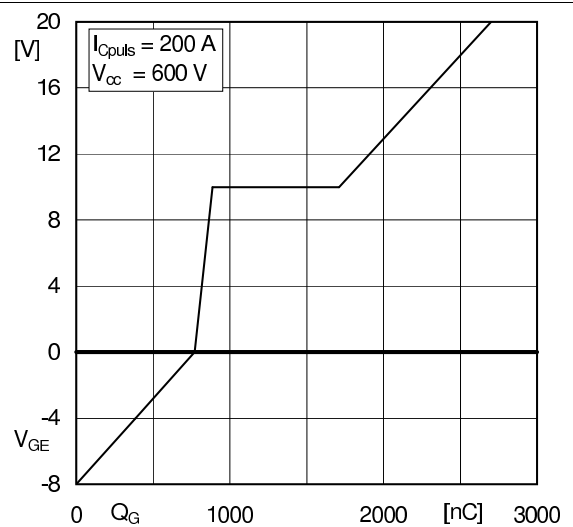


Fig. 6: Typ. gate charge characteristic

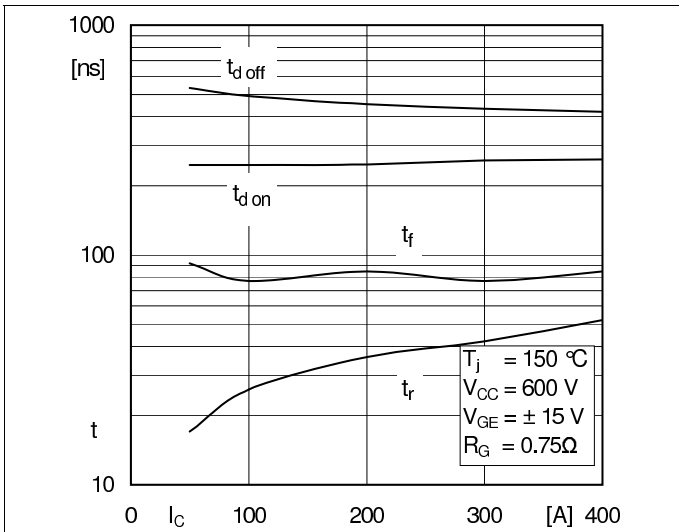


Fig. 7: Typ. switching times vs.  $I_C$

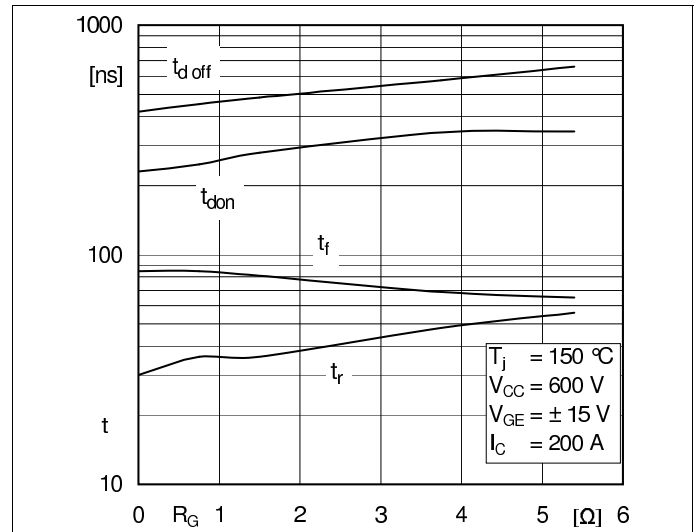


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

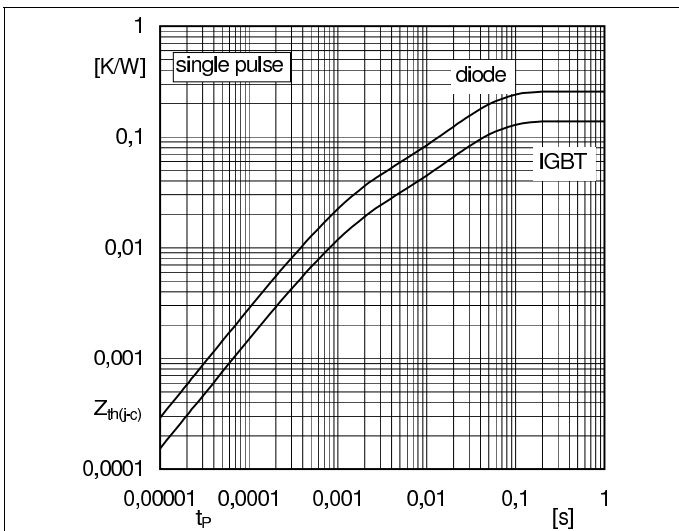


Fig. 9: Transient thermal impedance

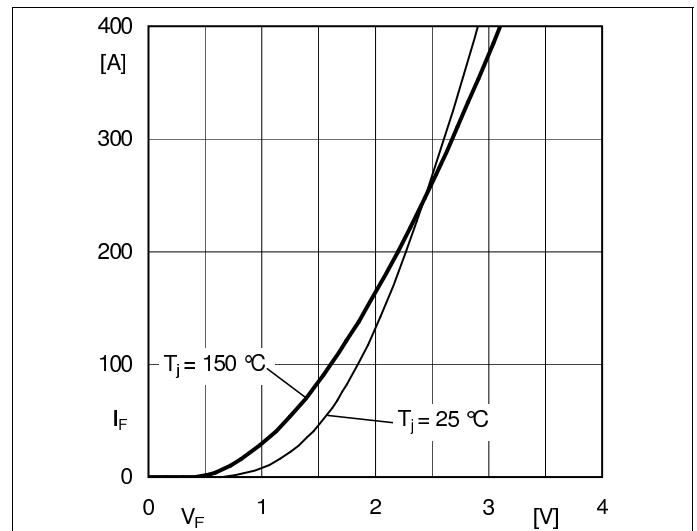


Fig. 10: Typ. CAL diode forward charact., incl.  $R_{CC+EE}$

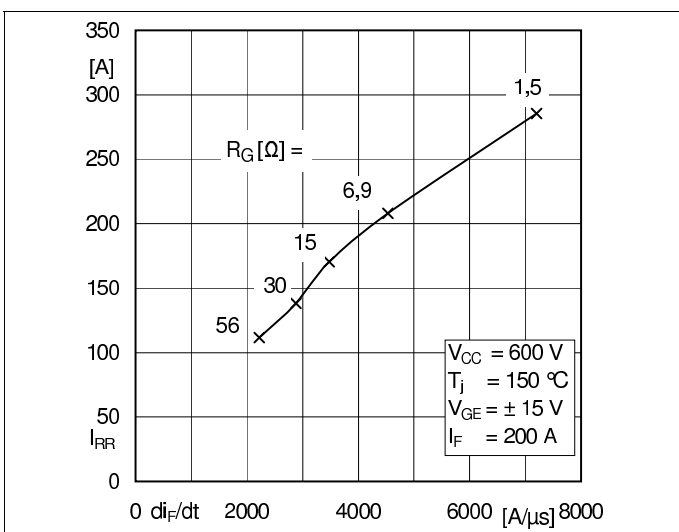


Fig. 11: CAL diode peak reverse recovery current

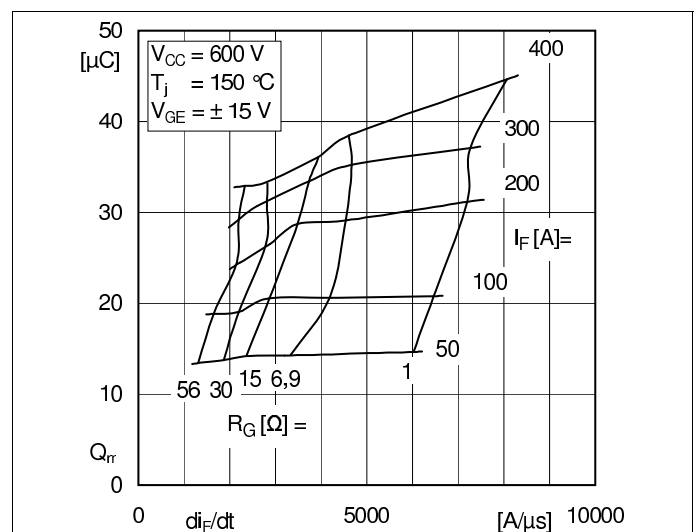


Fig. 12: Typ. CAL diode peak reverse recovery charge

